Kinetics model for selective thermal etching of $Si_{1-x}Ge_x$ in F_2/Ar

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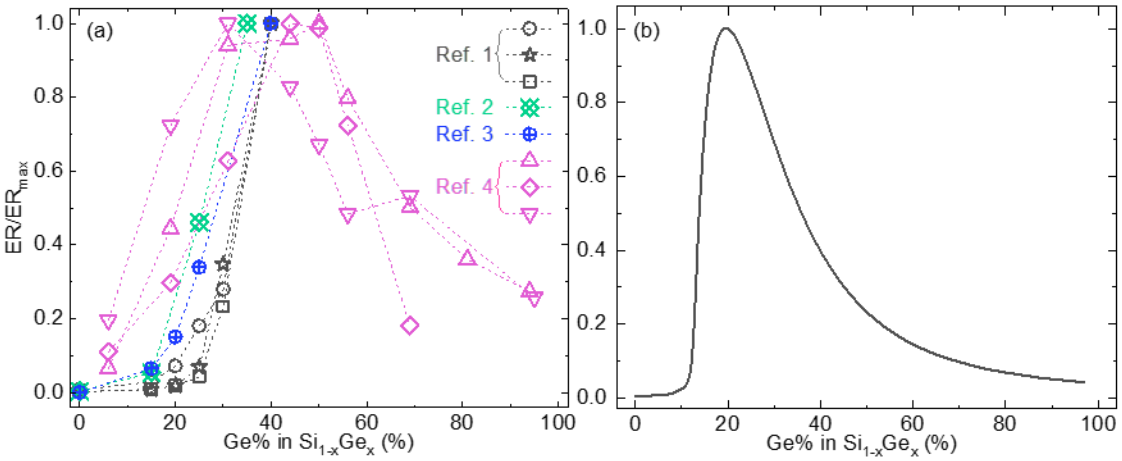

Fig. 1 (a) Etch rate (ER) of Si_xGe_{1-x} versus Ge% from literature, normalized to the maximum etch rate in each data set. The maximum etch selectivity based on reported etch rates (not shown) ranged 100 to 1000, observed at Ge% = 30 to 50 %. The symbols represent experimental data, while the dashed lines connecting the data points are visual aids to guide the eye. (b) Modeled ER/ER_{max} – fits over the unpublished experimental data will be presented at the conference.

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